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- 7. (a) Obtain the expression for noise margin high (NM_H) for a CMOS inverter from the voltage transfer characteristics.
 - (b) State how the Wilson MOS mirror can be modified to avoid the systematic current error. Derive an expression for output resistance in a Wilson MOS mirror.

Group - E

- 8 (a) Derive an expression for propagation delay in a CMOS inverter with capacitor load. Comment on the relation between propagation delay and capacitance of the load.
 - (b) Draw the CMOS realization to implement the following logic expression, $y = \overline{A(B + CD)}$

6 + 6 = 12

7 + (2 + 3) = 12

- 9 (a) Derive the expression for noise margin high from voltage transfer characteristics of a pseudo-NMOS inverter.
 - (b) Explain with detailed circuit diagram for a process of writing '0' in a 6T SRAM cell.

6 + 6 = 12

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MICRO ELECTRONIC DEVICES AND CIRCUITS (AEIE 5101)

Time Allotted: 3 hrs

Full Marks: 70

Figures out of the right margin indicate full marks.

Candidates are required to answer Group A and <u>Any 5 (five)</u> from Group B to E, taking <u>at least one</u> from each group.

Candidates are required to give answer in their own words as far as practicable.

Group – A (Multiple Choice Type Questions)

1. Choose the correct alternative for the following:

 $10 \times 1 = 10$

- (i) The threshold voltage of an n-channel MOSFET can be increased by
 (a) increasing the channel dopant concentration
 (b) reducing the channel dopant concentration
 (c) reducing gate oxide thickness
 (d) reducing the channel length.
- (ii) In a CMOS inverter the upper MOSFET is

 (a) active load
 (b) passive load
 (c) complementary load
 (d) none of the above.
- (iii) What is the difference voltage output from an Op-Amp if the inputs are an ideal in-phase signal?(a) The differential gain times twice the input signal
 - (b) The differential gain times the input signal
 - (c) The common-mode gain times twice the input signal

(d) The common-mode gain times the input signal.

- (iv) The primary function of the bias circuit is to (a) hold the circuit stable at V_{CC}
 - (b) hold the circuit stable at V_{in}
 - (c) ensure proper gain is achieved
 - (d) hold the circuit stable at the designed Q-point.
- (v) What is the voltage gain of the unity follower?
 (a) 0
 (b) 1
 (c) -1
 (d) infinity.

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(c) inductor

(vi) A MOSFET is

(a) a current-controlled device	(b) a voltage-controlled device
(c) always forward-biased	(d) reversed biased.

(vii) Which components are hard to fabricate into ICs? (a) diode

(b) resistor

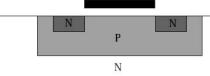
(d) transistor.

- (viii) What is the most common method used for the growth of single crystals for IC fabrication? (a) epitaxial growth (b) czochralsky pulling technique
 - (c) film deposition

(d) photolithography.

- (ix) Voltage follower is a special case of (a) inverting configuration (b) non-inverting configuration (d) integrator configuration.
 - (c) difference configuration
- (x)The MOSFET below

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is labeled with the different types of silicon. The device is best described as

(a) an n-MOSFET in an N-well (c) a p-MOSFET in an N-well

(b) an n-MOSFET in a P-well (d) a p-MOSFET in a P-well.

Group - B

- 2. (a) What are the various steps involved in IC fabrication process? Briefly describe each step.
 - Design an active resistor by using an n-channel MOSFET and derive (b) the expression for resistance.

5 + 7 = 12

- 3. (a) Derive the expression for current transfer ratio in a two transistor BJT Widlar current source.
 - For $I_{ref} = 1$ mA, find I_0 when $V_0 = 5V$. For a cascade MOS mirror utilizing (b) devices with $V_t = 0.5V$, $\mu_n C_{ox} = 387 \mu A/V^2$, $V_a' = 5V/\mu m$, $W/L = 3.6 \mu m/0.36 \mu m$ and I_{ref} = 100 µA, find output resistance of the MOS mirror. 6 + 6 = 12

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Group - C

- An active-loaded MOS differential amplifier inside 741 Op-Amp has the fol 4. (a) specification: $(W/L)_n = 100$, $(W/L)_P = 200$, $\mu_n C_{ox} = 2\mu_n C_{ox} = 0.2$ $V_{An} = |V_{Ap}| = 20 \text{ V}, \text{ I} = 0.8 \text{ mA}, \text{R}_{SS} = 25 \text{ k}\Omega.$ Calculate G_M, Ad, |A_{CM}| and CMRF MOS differential pair.
 - (b) Deduce the expression for the transconductance for the input st a 741 Op-Amp.

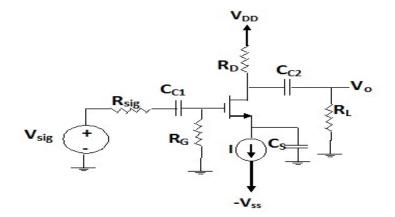
7 + 5

- 5. (a) Derive the expression for output resistance in a 741 Op-Amp fro small signal model of the output stage.
 - (b) Derive the relationship between unity-gain bandwidth (f_t) and rate (SR) in case of a 741 Op-Amp.

9+3

Group - D

- Derive the expression for CMRR of an active loaded MOS differ 6. (a) pair.
 - Perform small signal analysis on the given NMOS amplifier c (b) shown in following figure. Find an expression for output impe and voltage gain.



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